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2815

Attorney's Docket No. 5308-168

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Das et al.
Serial No.: 09/878,442
Filed: June 11, 2001

Group Art Unit: 2815
Confirmation No.: 2584
Examiner: J. Jackson, Jr.

For: HIGH VOLTAGE, HIGH TEMPERATURE CAPACITOR AND
INTERCONNECTION STRUCTURES

Date: July 29, 2002

BOX NON-FEE AMENDMENT
Commissioner for Patents
Washington, DC 20231

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TECHNOLOGY CENTER 2800

PATENT

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AMENDMENT AND REQUEST FOR RECONSIDERATION

Sir:

Applicants provide the present Amendment to address the issues raised in the Official Action mailed April 29, 2002. A copy of the amendments of the application is provided herewith and entitled "VERSION WITH MARKINGS TO SHOW CHANGES."

In the Title:

Please amend to title to recite as follows:

HIGH VOLTAGE, HIGH TEMPERATURE CAPACITOR AND
INTERCONNECTION STRUCTURES

In the Claims:

Please cancel the non-elected Claims 22-31 and 47-56.

Please amend Claim 1 to recite as follows:

1. (Amended) A capacitor having a dielectric structure comprising:
- a silicon carbide layer;
 - a first oxide layer having a first thickness directly on the silicon carbide layer;
 - a layer of dielectric material on the first oxide layer and having a second thickness, the layer of dielectric material having a dielectric constant higher than the dielectric constant of the first oxide layer;
 - a second oxide layer on the layer of dielectric material opposite the first oxide layer and having a third thickness; and

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